

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Original) An electro-optical apparatus, comprising:
  - a substrate;
  - a pixel electrode provided above the substrate;
  - a thin film transistor to perform switching control of the pixel electrode;
  - a data line provided on an upper layer side of the thin film transistor, and which supplies an image signal to the pixel electrode via the thin film transistor;
  - a storage capacitor, including a pixel-potential-side capacitor electrode, provided on the upper layer side of the thin film transistor, and which is electrically connected between the thin film transistor and the pixel electrode;
  - a dielectric film;
  - a capacitor line including a fixed-potential-side capacitor electrode provided on the upper layer side of the pixel-potential-side capacitor electrode, facing the pixel-potential-side capacitor electrode with the dielectric film disposed therebetween, and which is provided with a notch portion corresponding to a connection region to connect the pixel-potential-side capacitor electrode and the pixel electrode;
  - the pixel-potential-side capacitor electrode including a first conductive transparent film, the capacitor line including a first conductive light-shielding film, the data line including a second conductive light-shielding film, and the pixel electrode including a second conductive transparent film; and
  - a multilayer junction-layer transit-connected between the pixel-potential-side capacitor electrode and the pixel electrode, which has a laminated structure including a first layer including the second light-shielding film and a conductive second layer having a

chemical stability against the second transparent film higher than a chemical stability of the second light-shielding film, laminated on the upper layer side of the first layer, and which is planar covering the notch portion in plan view and is further provided in the connection region.

2. (Original) The electro-optical apparatus according to Claim 1,  
the multilayer junction-layer being larger than the notch portion in plan view.
3. (Original) The electro-optical apparatus according to Claim 1,  
the data line having the same laminated structure as the multilayer junction-layer.
4. (Original) The electro-optical apparatus according to Claim 1, further including:
  - a first interlayer insulating film laminated between the thin film transistor and the first transparent film;
  - a second interlayer insulating film laminated between the first light-shielding film and the second light-shielding film; and
  - a third interlayer insulating film laminated between the second light-shielding film and the second transparent film;
  - the thin film transistor and the pixel-potential-side capacitor electrode being electrically connected via a first contact hole provided in the first insulation film;
  - the pixel-potential-side capacitor electrode and the multilayer junction-layer being electrically connected via a second contact hole provided in the second interlayer insulating film; and
  - the multilayer junction-layer and the pixel electrode being electrically connected via a third contact hole provided in the third interlayer insulating film.

5. (Original) The electro-optical apparatus according to Claim 4,  
the third contact hole being provided extending in the second contact hole, and  
the first transparent film, the multilayer junction-layer and the second  
transparent film being directly laminated in the second contact hole.
6. (Original) The electro-optical apparatus according to Claim 5,  
the second contact hole and the third contact hole being coaxially provided.
7. (Original) The electro-optical apparatus according to Claim 1,  
the second transparent film including ITO (Indium Tin Oxide),  
the first layer including Al (aluminum), and  
the second layer including a simple metal, an alloy or a metal silicide, or a  
metal nitride film, which contains a high-melting-point metal.
8. (Original) The electro-optical apparatus according to Claim 1,  
the second layer having an OD (Optical Density) value of 2.0 or more.
9. (Original) The electro-optical apparatus according to Claim 1, further  
including:  
a facing-substrate facing the substrate; and  
an electro-optical material layer held between the substrate and the facing-  
substrate.
10. (Original) An electro-optical apparatus, comprising:  
a substrate;  
a pixel electrode provided above the substrate;  
a thin film transistor to perform switching control of the pixel electrode;  
a data line provided on an upper layer side of the thin film transistor, and  
which supplies an image signal to the pixel electrode via the thin film transistor;

a storage capacitor, including a pixel-potential-side capacitor electrode, provided on the upper layer side of the thin film transistor, and which is electrically connected between the thin film transistor and the pixel electrode;

a dielectric film;

a capacitor line including a fixed-potential-side capacitor electrode provided on the upper layer side of the pixel-potential-side capacitor electrode, facing the pixel-potential-side capacitor electrode with the dielectric film therebetween, and which is provided with a notch portion corresponding to a connection region to connect the pixel-potential-side capacitor electrode and the pixel electrode;

the pixel-potential-side capacitor electrode including a first conductive transparent film, the capacitor line including a first conductive light-shielding film, the data line including a second conductive light-shielding film, the pixel electrode including a second conductive transparent film; and

a monolayer junction-layer transit-connected between the pixel-potential-side capacitor electrode and the pixel electrode, which includes the second light-shielding film, and which is planar covering the notch portion in plan view and is further provided in the connection region.

11. (Original) The electro-optical apparatus according to Claim 10, the second transparent film including ITO, and the second light-shielding film including a simple metal, an alloy or a metal silicide, or a metal nitride film, which contains a high-melting-point metal.

12. (Original) The electro-optical apparatus according to Claim 10, further including:

a facing-substrate facing the substrate; and

an electro-optical material layer held between the substrate and the facing-substrate.

13. (Original) An electronic equipment, comprising:

an electro-optical apparatus that includes:

a substrate;

a pixel electrode provided above the substrate;

a thin film transistor to perform switching control of the pixel electrode;

a data line provided on an upper layer side of the thin film transistor, and which supplies an image signal to the pixel electrode via the thin film transistor;

a storage capacitor including a pixel-potential-side capacitor electrode, provided on the upper layer side of the thin film transistor, and which is electrically connected between the thin film transistor and the pixel electrode;

a dielectric film;

a capacitor line including a fixed-potential-side capacitor electrode provided on the upper layer side of the pixel-potential-side capacitor electrode, facing the pixel-potential-side capacitor electrode with the dielectric film disposed therebetween, and which is provided with a notch portion corresponding to a connection region to connect the pixel-potential-side capacitor electrode and the pixel electrode;

the pixel-potential-side capacitor electrode including a first conductive transparent film, the capacitor line including a first conductive light-shielding film, the data line including a second conductive light-shielding film, the pixel electrode including a second conductive transparent film; and

a multilayer junction-layer transit-connected between the pixel-potential-side capacitor electrode and the pixel electrode, which has a laminated structure including a first

layer including the second light-shielding film and a conductive second layer having chemical stability against the second transparent film higher than a chemical stability of the second light-shielding film, laminated on the upper layer side of the first layer, and which is planar covering the notch portion in plan view and is further provided in the connection region.

14. (Original) An electronic equipment, comprising:

an electro-optical apparatus that includes:

a substrate;

a pixel electrode provided above the substrate;

a thin film transistor to perform switching control of the pixel electrode;

a data line provided on an upper layer side of the thin film transistor, and which supplies an image signal to the pixel electrode via the thin film transistor;

a storage capacitor, including a pixel-potential-side capacitor electrode, which is provided on the upper layer side of the thin film transistor, and which is electrically connected between the thin film transistor and the pixel electrode;

a dielectric film;

a capacitor line including a fixed-potential-side capacitor electrode provided on the upper layer side of the pixel-potential-side capacitor electrode, facing the pixel-potential-side capacitor electrode with the dielectric film therebetween, and which is provided with a notch portion corresponding to a connection region to connect the pixel-potential-side capacitor electrode and the pixel electrode;

the pixel-potential-side capacitor electrode including a first conductive transparent film, the capacitor line including a first conductive light-shielding film, the data line including a second conductive light-shielding film, the pixel electrode including a second conductive transparent film; and

a monolayer junction-layer transit-connected between the pixel-potential-side capacitor electrode and the pixel electrode, which includes the second light-shielding film, and which is planar covering the notch portion in plan view and is further provided in the connection region.

15. (New) An electro-optical apparatus, comprising:

a substrate;

a pixel electrode provided above the substrate;

a thin film transistor to perform switching control of the pixel electrode;

a data line provided on an upper layer side of the thin film transistor, and

which supplies an image signal to the pixel electrode via the thin film transistor;

a pixel-potential-side capacitor electrode which is provided with a notch portion corresponding to a connection region to connect the pixel-potential-side capacitor electrode and the pixel electrode, facing the pixel-potential-side capacitor electrode with a dielectric film disposed therebetween, provided on the upper layer side of the thin film transistor, and which is electrically connected between the thin film transistor and the pixel electrode; and

a junction-layer connected between the pixel-potential-side capacitor electrode and the pixel electrode, which includes a light shielding film, and which is planar covering the notch portion in plan view and is further provided in the connection region.